

計算機アーキテクチャ 第一 (E)

6. メモリ2: 半導体メモリシステム, ファイルメモリシステム

吉瀬 謙二 計算工学専攻
kise_at_cs.titech.ac.jp
W641講義室 木曜日13:20 - 14:50

Acknowledgement

- **Lecture slides** for Computer Organization and Design, Third Edition, courtesy of **Professor Mary Jane Irwin**, Penn State University
- **Lecture slides** for Computer Organization and Design, third edition, Chapters 1-9, courtesy of **Professor Tod Amon**, Southern Utah University.

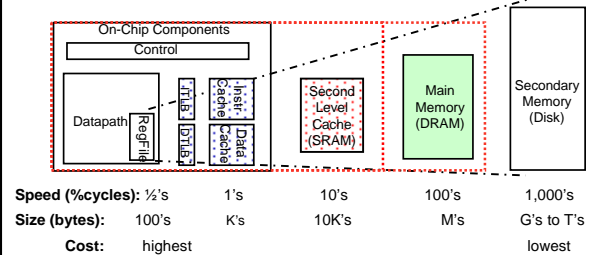
Adapted from Computer Organization and Design, Patterson & Hennessy, © 2005

The Memory Hierarchy Goal

- **Fact:**
Large memories are slow and fast memories are small
- How do we create a memory that gives the illusion of being large, cheap and fast ?
 - With **hierarchy** (階層)
 - With **parallelism** (並列性)

A Typical Memory Hierarchy

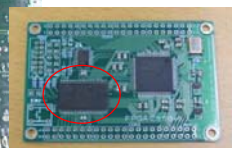
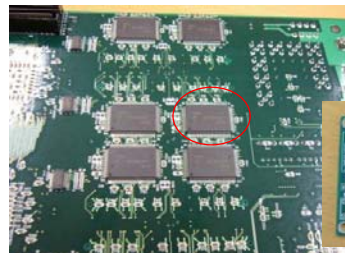
- By taking advantage of **the principle of locality** (局所性)
 - Present **much memory in the cheapest technology**
 - at **the speed of fastest technology**



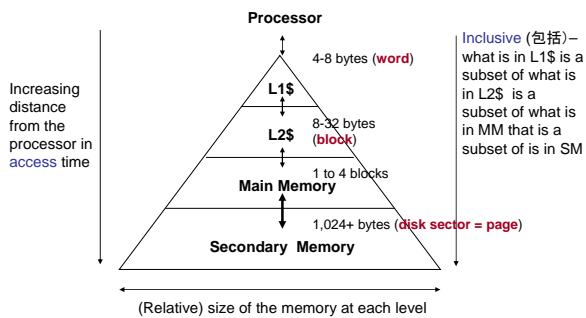
DRAM (dynamic random access memory)



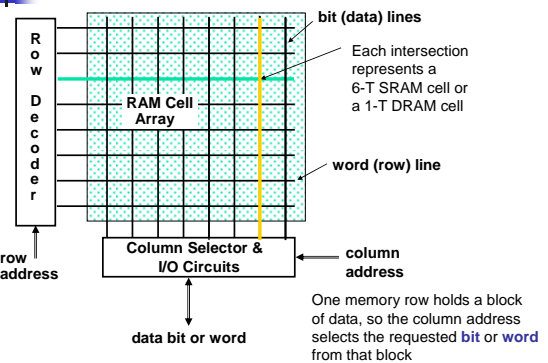
SRAM (static random access memory)



Characteristics of the Memory Hierarchy

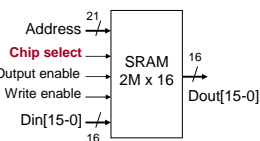


Classical RAM Organization (~Square)

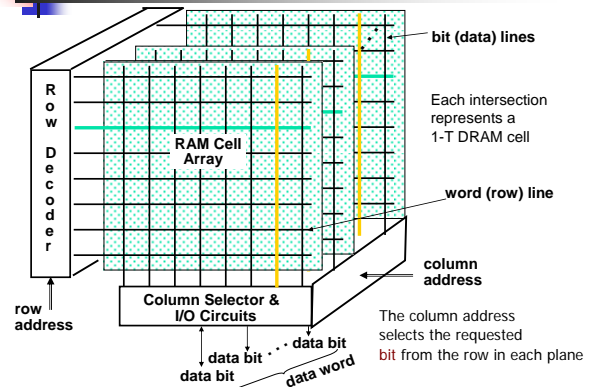


Memory Hierarchy Technologies

- Caches use **SRAM** for speed and technology compatibility
 - Low density** (**6 transistor cells**), high power, expensive, fast
 - Static**: content will last "forever" (until power turned off)
- Main Memory uses **DRAM** for size (density)
 - High density** (**1 transistor cells**), low power, cheap, slow
 - Dynamic**: needs to be "refreshed" regularly (~ every 8 ms)
 - 1% to 2% of the active cycles of the DRAM
 - Addresses divided into 2 halves (row and column)
 - RAS** or **Row Access Strobe** triggering row decoder
 - CAS** or **Column Access Strobe** triggering column selector



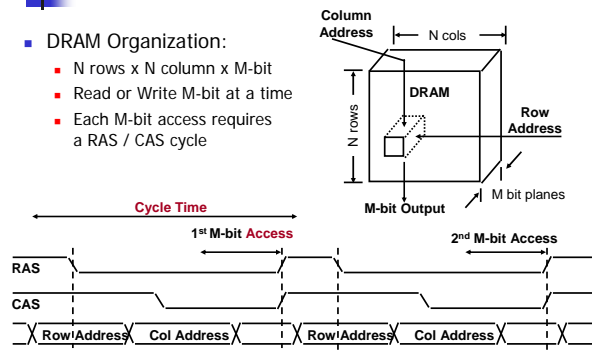
Classical DRAM Organization (~Square Planes)



Classical DRAM Operation

DRAM Organization:

- N rows x N column x M-bit
- Read or Write M-bit at a time
- Each M-bit access requires a RAS / CAS cycle



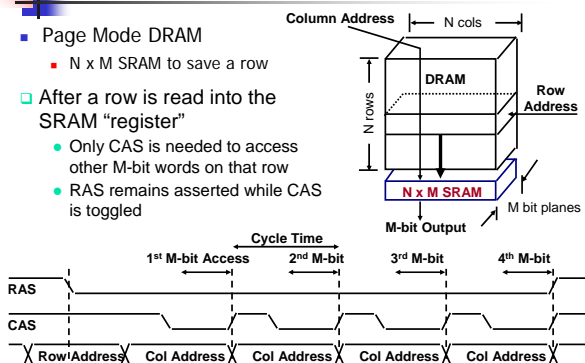
Page Mode DRAM Operation

Page Mode DRAM

- N x M SRAM to save a row

After a row is read into the SRAM "register"

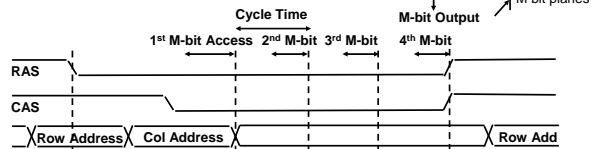
- Only CAS is needed to access other M-bit words on that row
- RAS remains asserted while CAS is toggled



Synchronous DRAM (SDRAM) Operation

- After a **row** is read into the SRAM register

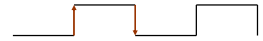
- Inputs CAS as the starting "burst" address along with a burst length
- Transfers a burst of data from a series of sequential addresses within that row



Other DRAM Architectures

- Double Data Rate SDRAMs – **DDR-SDRAMs** (and DDR-SRAMs)
 - Double data rate because they transfer data on both the rising and falling edge of the clock
 - Are the most widely used form of SDRAMs

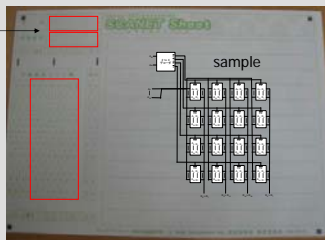
- DDR2-SDRAMs**
- DDR3-SDRAMs**



演習

- 512K x 8ビット (512KB) のSRAMを用いて、32ビットデータ幅の4MBのメモリを実現したい。
- 8個のメモリチップ、チップ選択信号CS、データ信号、アドレス信号の接続を示せ。

氏名, 学籍番号,
学籍番号マーク欄(右詰で)



DRAM Memory Latency & Bandwidth Milestones

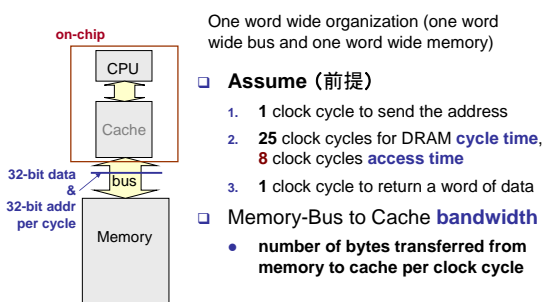
	DRAM	Page DRAM	FastPage DRAM	FastPage DRAM	Synch DRAM	DDR SDRAM
Module Width	16b	16b	32b	64b	64b	64b
Year	1980	1983	1986	1993	1997	2000
Mb/chip	0.06	0.25	1	16	64	256
Die size (mm ²)	35	45	70	130	170	204
Pins/chip	16	16	18	20	54	66
BWidth (MB/s)	13	40	160	267	640	1600
Latency (nsec)	225	170	125	75	62	52

Patterson, CACM Vol 47, #10, 2004

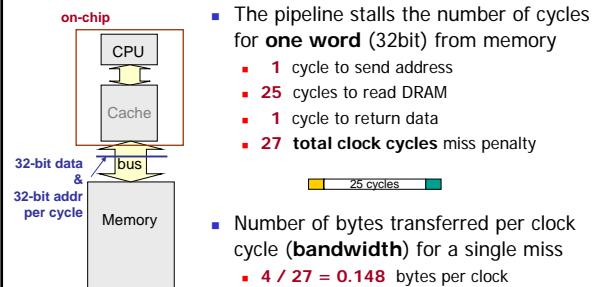
- In the time that the memory to processor **bandwidth** doubles the memory **latency** improves by a factor of only 1.2 to 1.4
- To deliver such high bandwidth, the internal DRAM has to be organized as **interleaved memory banks**

Memory Systems that Support Caches

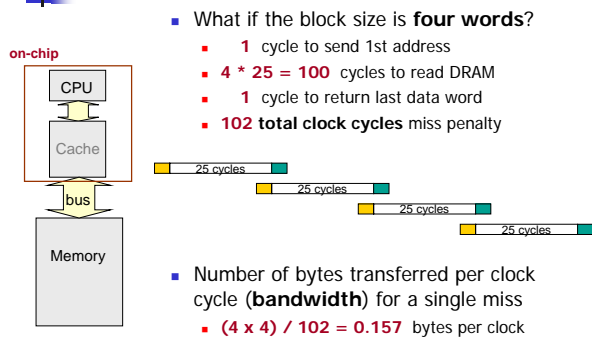
- The off-chip interconnect and memory architecture can affect overall system performance **in dramatic ways**



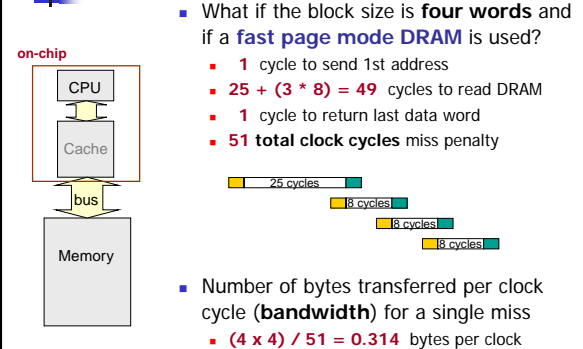
One Word Wide Memory Organization



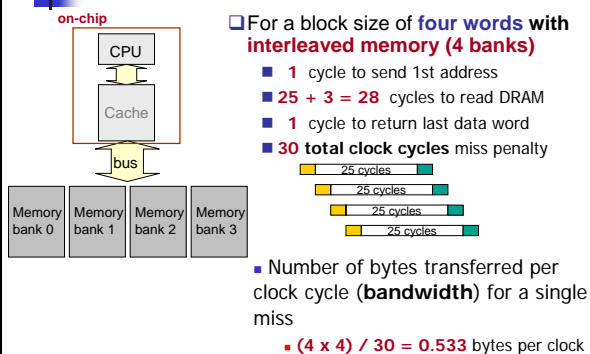
One Word Wide Memory Organization, con't



One Word Wide Memory Organization, con't



Interleaved (インターリーブ) Memory Organization



アナウンス

- 講義スライドおよびスケジュール
 - www.arch.cs.titech.ac.jp
 - 講義日程が変更になることがあるので頻繁に確認すること。